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Atty Docket 0819-0724

Serial No. 10/019,540

INFORMATION DISCLOSURE STATEMENT

Applicants: Takashi NISHIKAWA

Filing Date: January 03, 2002

Group Art Unit: N/A

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
	02-244674	09/28/1990	JP			Part Eng

OTHER DOCUMENT

(Including Author, Title, Date, Pertinent Pages, Etc.)

Examiner Initial	
Gu	"Table 22 Thermal/Thin Films Gate Etch and Doping Technology Requirement", p. 74, The National Technology Roadmap for Semiconductors Technology Needs
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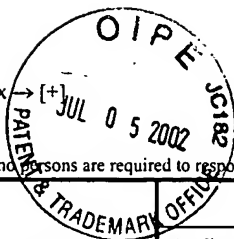
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known			
				Application Number		10/019,540	
				Filing Date		January 3, 2002	
				First Named Inventor		Takashi NISHIKAWA	
				Group Art Unit		2811	
Examiner Name							
Sheet	1	of	1	Attorney Docket Number		740819-724	

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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San		5,616,947		Tamura	04-01-1997	

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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
San			11-162852		Japan	06-18-1999		
			64-82671		Japan	03-28-1989		
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San			1-211976		Japan	08-25-1989		

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